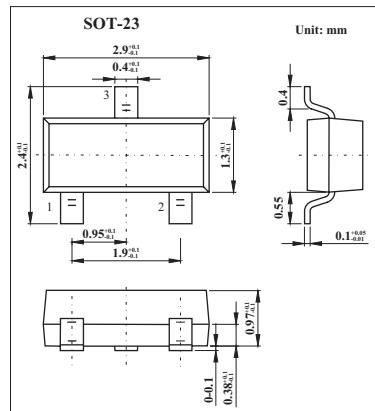
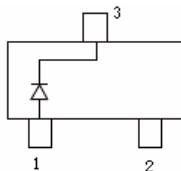


Surface Mount Switching Diode

DAN212K

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V _{RWM}	75	V
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	53	V
Average Rectified Output Current	I _O	200	mA
Forward Continuous Current	I _{FM}	300	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0 μ s @ t = 1.0s	I _{FSM}	2.0 1.0	A
Power Dissipation	P _d	225	mW
Thermal Resistance Junction to Ambient Air	R _{θ JA}	556	°C/W
Operating and Storage Temperature Range	T _{TSTG}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{(BR)R}	I _R =100 μ A	75			V
Forward Voltage	V _F	I _F = 1.0mA I _F = 10mA I _F = 50mA I _F = 150mA			0.715 0.855 1.0 1.25	V
Leakage Current	I _R	V _R = 75V V _R = 20V			1.0 25	μ A nA
Junction Capacitance	C _j	V _R = 0, f = 1.0MHz			2	pF
Reverse Recovery Time	t _{rr}	I _F = I _R = 10mA, I _{rr} = 0.1 X I _R , R _L = 100 Ω			4	ns

■ Marking

Marking	A6
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■ Typical Characteristics

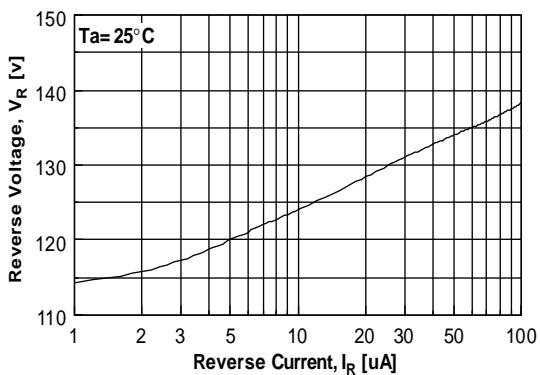


Figure 1. Reverse Voltage vs Reverse Current
BV - 1.0 to 100 uA

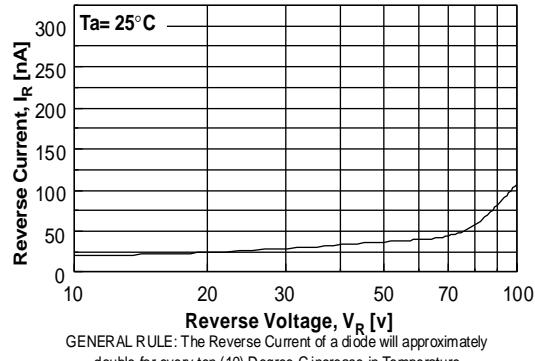


Figure 2. Reverse Current vs Reverse Voltage
IR - 10 to 100 V

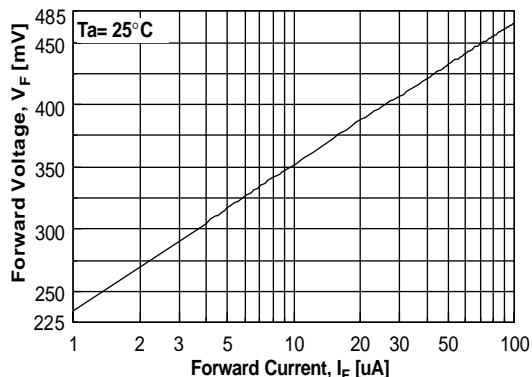


Figure 3. Forward Voltage vs Forward Current
VF - 1.0 to 100 uA

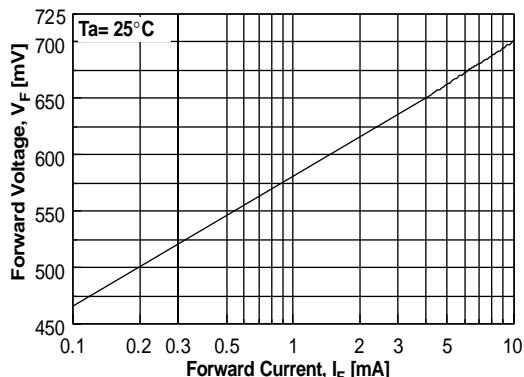


Figure 4. Forward Voltage vs Forward Current
VF - 0.1 to 10 mA

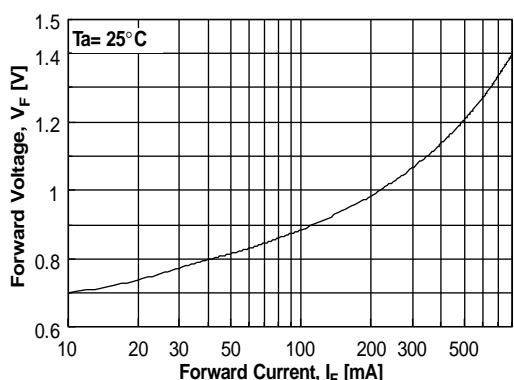


Figure 5. Forward Voltage vs Forward Current
VF - 10 - 800 mA

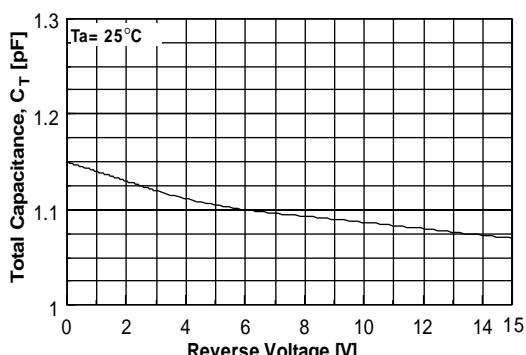
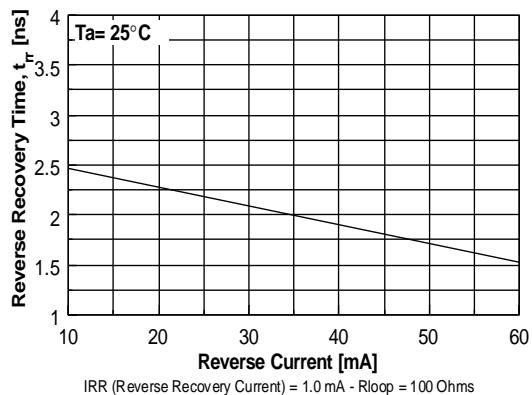
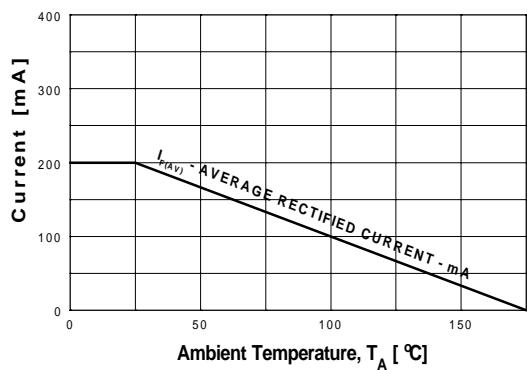


Figure 6. Total Capacitance

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**Figure 7. Reverse Recovery Time
vs Reverse Current**
TRR - IR 10 mA vs 60 mA



**Figure 8. Average Rectified Current (I_{F(AV)})
versus Ambient Temperature (T_A)**

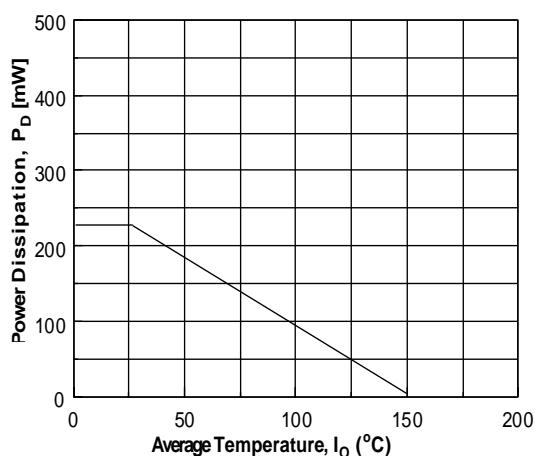


Figure 9. Power Derating Curve